

# NSS12100XV6T1G

## Low $V_{CE(sat)}$ Transistor, PNP, 12 V, 1.0 A, SOT-563 Package

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are miniature surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

- High Current Capability (1 A)
- High Power Handling (Up to 650 mW)
- Low  $V_{CE(s)}$  (150 mV Typical @ 500 mA)
- Small Size
- This is a Pb-Free Device

### Benefits

- High Specific Current and Power Capability Reduces Required PCB Area
- Reduced Parasitic Losses Increases Battery Life

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

| Rating                                   | Symbol            | Max                       | Unit |
|------------------------------------------|-------------------|---------------------------|------|
| Collector-Emitter Voltage                | $V_{CEO}$         | -12                       | Vdc  |
| Collector-Base Voltage                   | $V_{CBO}$         | -12                       | Vdc  |
| Emitter-Base Voltage                     | $V_{EBO}$         | -5.0                      | Vdc  |
| Collector Current – Continuous<br>– Peak | $I_C$<br>$I_{CM}$ | -1.0<br>-2.0              | Adc  |
| Electrostatic Discharge                  | ESD               | HBM Class 3<br>MM Class C |      |

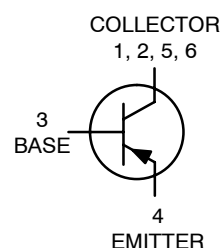
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

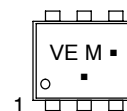
<http://onsemi.com>

**12 VOLTS, 1.0 AMPS**  
**PNP LOW  $V_{CE(sat)}$  TRANSISTOR**  
**EQUIVALENT  $R_{DS(on)}$  300 m $\Omega$**



**SOT-563**  
**CASE 463A**  
**STYLE 4**

### DEVICE MARKING



VE = Specific Device Code  
M = Month Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

| Device         | Package              | Shipping†        |
|----------------|----------------------|------------------|
| NSS12100XV6T1G | SOT-563<br>(Pb-Free) | 4000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# THERMAL CHARACTERISTICS

| Characteristic                                                                              | Symbol                   | Max         | Unit                         |
|---------------------------------------------------------------------------------------------|--------------------------|-------------|------------------------------|
| Total Device Dissipation<br>$T_A = 25^{\circ}\text{C}$<br>Derate above $25^{\circ}\text{C}$ | $P_D$ (Note 1)           | 500<br>4.0  | mW<br>mW/ $^{\circ}\text{C}$ |
| Thermal Resistance,<br>Junction-to-Ambient                                                  | $R_{\theta JA}$ (Note 1) | 250         | $^{\circ}\text{C/W}$         |
| Total Device Dissipation<br>$T_A = 25^{\circ}\text{C}$<br>Derate above $25^{\circ}\text{C}$ | $P_D$ (Note 2)           | 650<br>5.2  | mW<br>mW/ $^{\circ}\text{C}$ |
| Thermal Resistance,<br>Junction-to-Ambient                                                  | $R_{\theta JA}$ (Note 2) | 192         | $^{\circ}\text{C/W}$         |
| Thermal Resistance,<br>Junction-to-Lead 6                                                   | $R_{\theta JL}$          | 105         | $^{\circ}\text{C/W}$         |
| Total Device Dissipation<br>(Single Pulse < 10 sec.)                                        | $P_D$ Single             | 1.0         | W                            |
| Junction and Storage<br>Temperature Range                                                   | $T_J, T_{stg}$           | -55 to +150 | $^{\circ}\text{C}$           |

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                               |               |      |       |      |                 |
|-------------------------------------------------------------------------------|---------------|------|-------|------|-----------------|
| Collector-Emmitter Breakdown Voltage, ( $I_C = -10\text{ mAdc}$ , $I_B = 0$ ) | $V_{(BR)CEO}$ | -12  | -     | -    | Vdc             |
| Collector-Base Breakdown Voltage, ( $I_C = -0.1\text{ mAdc}$ , $I_E = 0$ )    | $V_{(BR)CBO}$ | -12  | -     | -    | Vdc             |
| Emitter-Base Breakdown Voltage, ( $I_E = -0.1\text{ mAdc}$ , $I_C = 0$ )      | $V_{(BR)EBO}$ | -5.0 | -     | -    | Vdc             |
| Collector Cutoff Current, ( $V_{CB} = -12\text{ Vdc}$ , $I_E = 0$ )           | $I_{CBO}$     | -    | -0.02 | -0.1 | $\mu\text{Adc}$ |
| Emitter Cutoff Current, ( $V_{CES} = -5.0\text{ Vdc}$ , $I_E = 0$ )           | $I_{EBO}$     | -    | -0.03 | -0.1 | $\mu\text{Adc}$ |

### ON CHARACTERISTICS

|                                                                                                                                                                                                                                                                                                                                             |               |                       |                                                |                                                |    |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-----------------------|------------------------------------------------|------------------------------------------------|----|
| DC Current Gain (Note 3)<br>( $I_C = -10\text{ mA}$ , $V_{CE} = -2.0\text{ V}$ )<br>( $I_C = -500\text{ mA}$ , $V_{CE} = -2.0\text{ V}$ )<br>( $I_C = -1.0\text{ A}$ , $V_{CE} = -2.0\text{ V}$ )                                                                                                                                           | $h_{FE}$      | 200<br>100<br>90      | -<br>-<br>-                                    | -<br>-<br>-                                    |    |
| Collector-Emmitter Saturation Voltage (Note 3)<br>( $I_C = -0.05\text{ A}$ , $I_B = -0.005\text{ A}$ ) (Note 4)<br>( $I_C = -0.1\text{ A}$ , $I_B = -0.002\text{ A}$ )<br>( $I_C = -0.1\text{ A}$ , $I_B = -0.010\text{ A}$ )<br>( $I_C = -0.5\text{ A}$ , $I_B = -0.050\text{ A}$ )<br>( $I_C = -1.0\text{ A}$ , $I_B = -0.100\text{ A}$ ) | $V_{CE(sat)}$ | -<br>-<br>-<br>-<br>- | -0.030<br>-0.080<br>-0.050<br>-0.200<br>-0.400 | -0.040<br>-0.100<br>-0.060<br>-0.225<br>-0.440 | V  |
| Base-Emmitter Saturation Voltage (Note 3)<br>( $I_C = -1.0\text{ A}$ , $I_B = -0.01\text{ A}$ )                                                                                                                                                                                                                                             | $V_{BE(sat)}$ | -                     | 0.95                                           | -1.15                                          | V  |
| Base-Emmitter Turn-on Voltage (Note 3)<br>( $I_C = -2.0\text{ A}$ , $V_{CE} = -3.0\text{ V}$ )                                                                                                                                                                                                                                              | $V_{BE(on)}$  | -                     | -1.05                                          | -1.15                                          | V  |
| Input Capacitance ( $V_{EB} = -0.5\text{ V}$ , $f = 1.0\text{ MHz}$ )                                                                                                                                                                                                                                                                       | $C_{ibo}$     | -                     |                                                | 50                                             | pF |
| Output Capacitance ( $V_{CB} = -3.0\text{ V}$ , $f = 1.0\text{ MHz}$ )                                                                                                                                                                                                                                                                      | $C_{obo}$     | -                     |                                                | 20                                             | pF |

- FR-4 @ 100 mm<sup>2</sup>, 1 oz copper traces.
- FR-4 @ 500 mm<sup>2</sup>, 1 oz copper traces.
- Pulsed Condition: Pulse Width = 300  $\mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .
- Guaranteed by design but not tested.

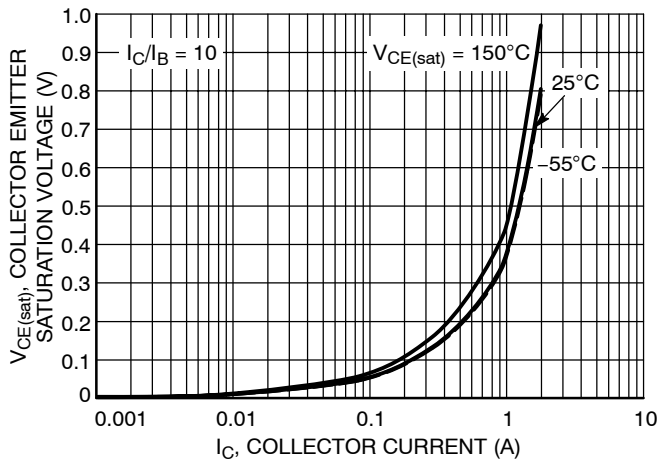


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

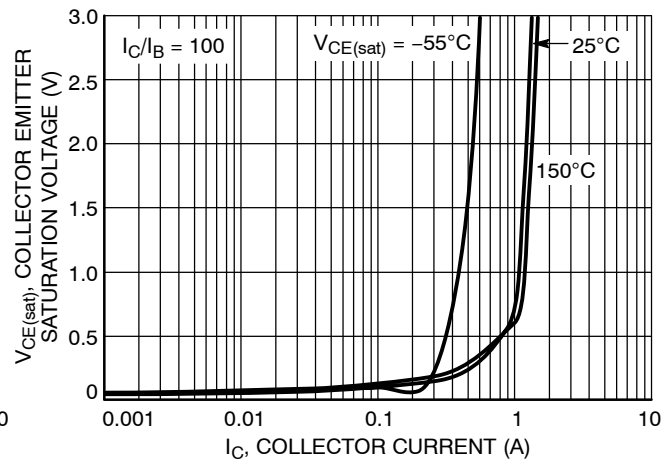


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

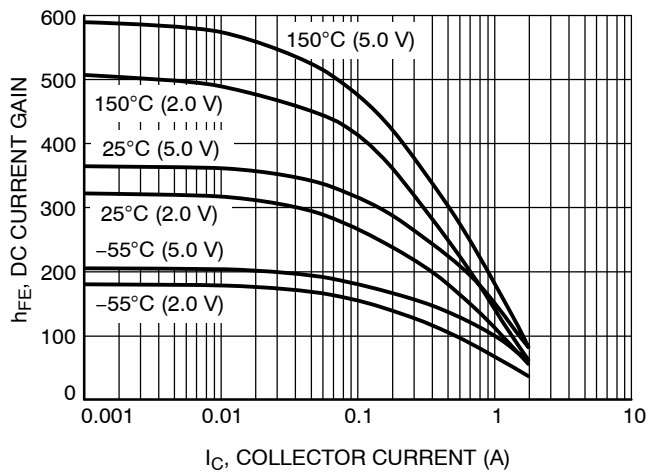


Figure 3. DC Current Gain vs. Collector Current

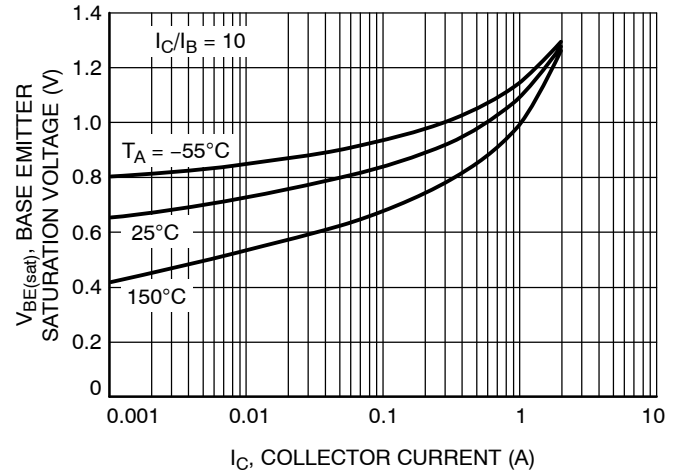


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

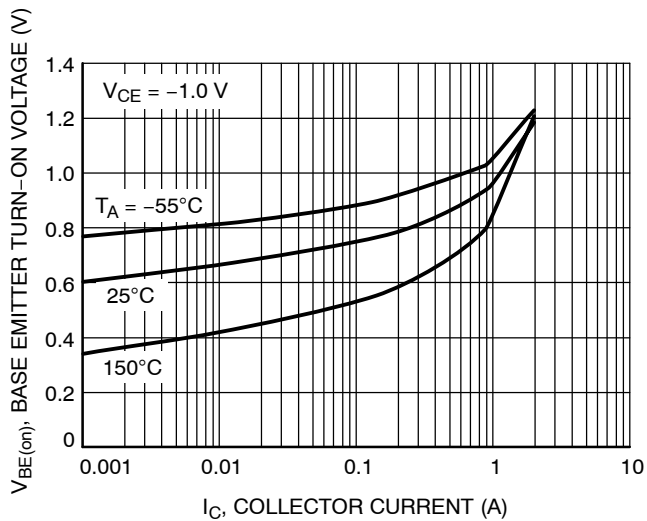


Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

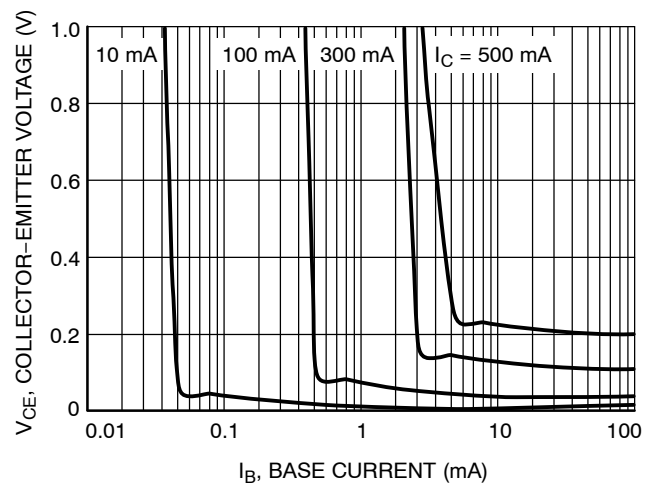
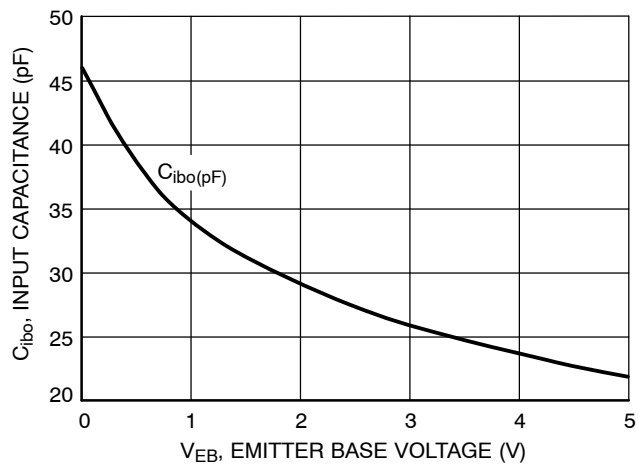
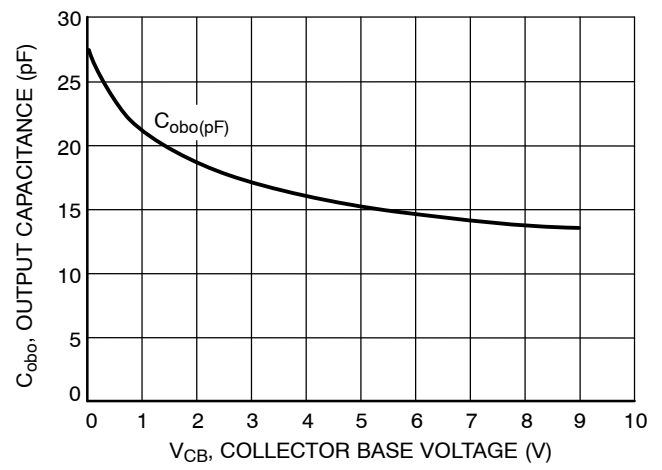


Figure 6. Saturation Region

# NSS12100XV6T1G



**Figure 7. Input Capacitance**



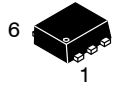
**Figure 8. Output Capacitance**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®

ON



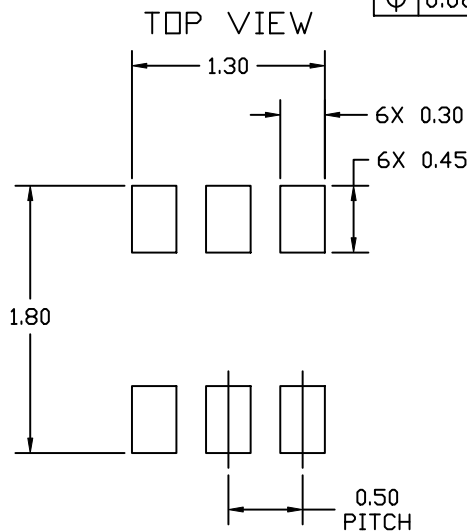
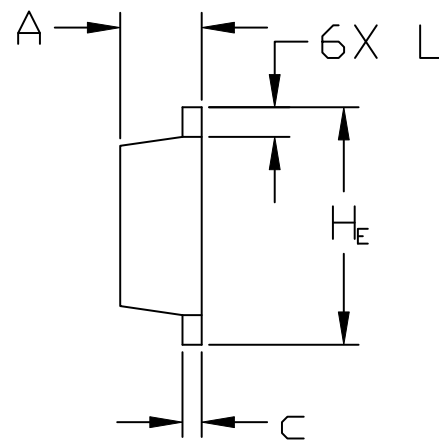
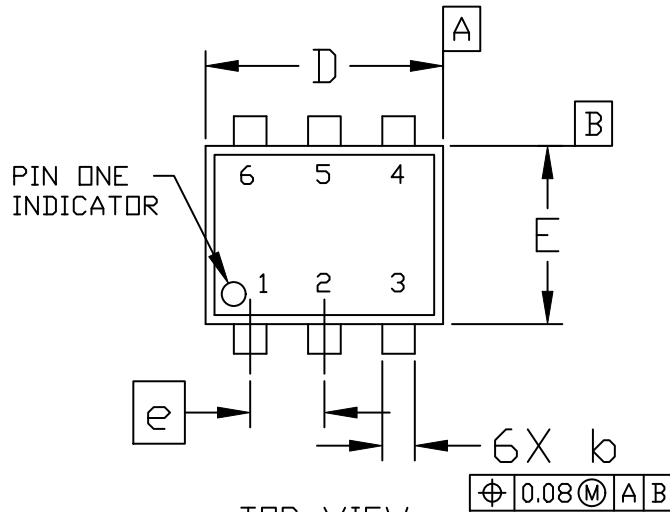
SCALE 4:1

**SOT-563, 6 LEAD**  
CASE 463A  
ISSUE H

DATE 26 JAN 2021

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



SIDE VIEW

| DIM            | MILLIMETERS |      |      |
|----------------|-------------|------|------|
|                | MIN.        | NOM. | MAX. |
| A              | 0.50        | 0.55 | 0.60 |
| b              | 0.17        | 0.22 | 0.27 |
| c              | 0.08        | 0.13 | 0.18 |
| D              | 1.50        | 1.60 | 1.70 |
| E              | 1.10        | 1.20 | 1.30 |
| e              | 0.50 BSC    |      |      |
| L              | 0.10        | 0.20 | 0.30 |
| H <sub>E</sub> | 1.50        | 1.60 | 1.70 |

### RECOMMENDED MOUNTING FOOTPRINT\*

- \* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

|                         |                        |                                                                                                                                                                                  |
|-------------------------|------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <b>DOCUMENT NUMBER:</b> | <b>98AON11126D</b>     | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| <b>DESCRIPTION:</b>     | <b>SOT-563, 6 LEAD</b> | <b>PAGE 1 OF 2</b>                                                                                                                                                               |

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**SOT-563, 6 LEAD**  
CASE 463A  
ISSUE H

DATE 26 JAN 2021

STYLE 1:  
PIN 1. EMITTER 1  
2. BASE 1  
3. COLLECTOR 2  
4. EMITTER 2  
5. BASE 2  
6. COLLECTOR 1

STYLE 2:  
PIN 1. EMITTER 1  
2. EMITTER 2  
3. BASE 2  
4. COLLECTOR 2  
5. BASE 1  
6. COLLECTOR 1

STYLE 3:  
PIN 1. CATHODE 1  
2. CATHODE 1  
3. ANODE/ANODE 2  
4. CATHODE 2  
5. CATHODE 2  
6. ANODE/ANODE 1

STYLE 4:  
PIN 1. COLLECTOR  
2. COLLECTOR  
3. BASE  
4. EMITTER  
5. COLLECTOR  
6. COLLECTOR

STYLE 5:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE  
4. ANODE  
5. CATHODE  
6. CATHODE

STYLE 6:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. CATHODE  
5. CATHODE  
6. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. CATHODE  
5. ANODE  
6. CATHODE

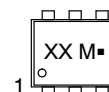
STYLE 8:  
PIN 1. DRAIN  
2. DRAIN  
3. GATE  
4. SOURCE  
5. DRAIN  
6. DRAIN

STYLE 9:  
PIN 1. SOURCE 1  
2. GATE 1  
3. DRAIN 2  
4. SOURCE 2  
5. GATE 2  
6. DRAIN 1

STYLE 10:  
PIN 1. CATHODE 1  
2. N/C  
3. CATHODE 2  
4. ANODE 2  
5. N/C  
6. ANODE 1

STYLE 11:  
PIN 1. EMITTER 2  
2. BASE 2  
3. COLLECTOR 1  
4. EMITTER 1  
5. BASE 1  
6. COLLECTOR 2

**GENERIC  
MARKING DIAGRAM\***



XX = Specific Device Code  
M = Month Code  
■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

|                         |                        |                                                                                                                                                                                     |
|-------------------------|------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <b>DOCUMENT NUMBER:</b> | <b>98AON11126D</b>     | Electronic versions are uncontrolled except when accessed directly from the Document Repository.<br>Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| <b>DESCRIPTION:</b>     | <b>SOT-563, 6 LEAD</b> | <b>PAGE 2 OF 2</b>                                                                                                                                                                  |

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**onsemi Website:** [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

**North American Technical Support:**

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

**Europe, Middle East and Africa Technical Support:**

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative